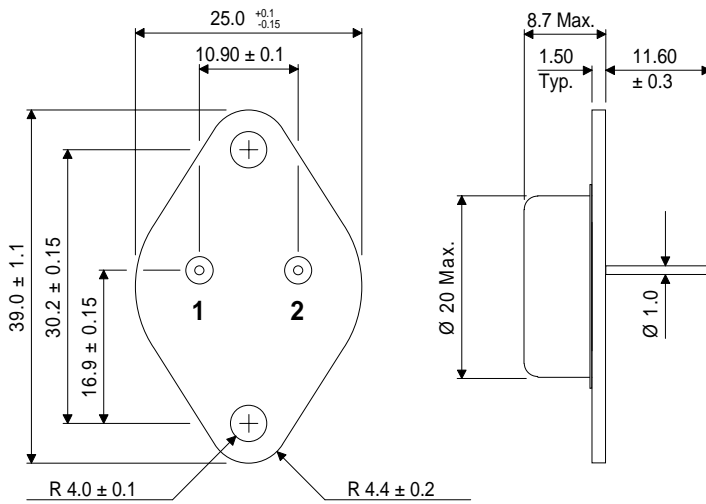


**MECHANICAL DATA**  
Dimensions in mm

**P-CHANNEL**  
**POWER MOSFET**



**POWER MOSFETS FOR**  
**AUDIO APPLICATIONS**

**FEATURES**

- HIGH SPEED SWITCHING
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (220V & 250V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODES
- COMPLIMENTARY N-CHANNEL BUZ902 & BUZ903

**TO-3**

Pin 1 – Gate

Pin 2 – Drain

Case – Source

**ABSOLUTE MAXIMUM RATINGS**

(T<sub>case</sub> = 25°C unless otherwise stated)

		<b>BUZ907</b>	<b>BUZ908</b>
V <sub>DSX</sub>	Drain – Source Voltage	-220V	-250V
V <sub>GSS</sub>	Gate – Source Voltage	±14V	
I <sub>D</sub>	Continuous Drain Current	-8A	
I <sub>D(PK)</sub>	Body Drain Diode	-8A	
P <sub>D</sub>	Total Power Dissipation @ T <sub>case</sub> = 25°C	125W	
T <sub>stg</sub>	Storage Temperature Range	-55 to 150°C	
T <sub>j</sub>	Maximum Operating Junction Temperature	150°C	
R <sub>θJC</sub>	Thermal Resistance Junction – Case	1°C/W	

**STATIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
BV <sub>DSX</sub> Drain – Source Breakdown Voltage	V <sub>GS</sub> = 10V I <sub>D</sub> = -10mA	BUZ907	-220			V
		BUZ908	-250			V
BV <sub>GSS</sub> Gate – Source Breakdown Voltage	V <sub>DS</sub> = 0	I <sub>G</sub> = ±100μA	±14			V
V <sub>GS(OFF)</sub> Gate – Source Cut-Off Voltage	V <sub>DS</sub> = -10V	I <sub>D</sub> = -100mA	-0.15		-1.5	V
V <sub>DS(SAT)</sub> * Drain – Source Saturation Voltage	V <sub>GD</sub> = 0	I <sub>D</sub> = -8A			-12	V
R <sub>DS(on)</sub> * Static – Source Resistance	V <sub>GS</sub> = -10	I <sub>D</sub> = -8A			1.5	Ω
I <sub>DSX</sub> Drain – Source Cut-Off Current	V <sub>GS</sub> = 10V	V <sub>DS</sub> = -220V BUZ907			-10	mA
		V <sub>DS</sub> = -250V BUZ908			-10	mA
y <sub>fs</sub> * Forward Transfer Admittance	V <sub>DS</sub> = -10V	I <sub>D</sub> = -3A	0.7		2	S

**DYNAMIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C <sub>iSS</sub> Input Capacitance	V <sub>DS</sub> = -10V f = 1MHz			TBA		pF
C <sub>oss</sub> Output Capacitance				TBA		
C <sub>rSS</sub> Reverse Transfer Capacitance				TBA		
t <sub>on</sub> Turn-on Time	V <sub>DS</sub> = -20V I <sub>D</sub> = -5A			TBA		ns
t <sub>off</sub> Turn-off Time				TBA		

\* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.

